

In the Specification:

Please insert before the first paragraph of the application:

This application is the national stage application of international application number PCT/EP2003/011381, filed on October 14, 2003, which claims the benefit of priority to German Patent Application 102 47 889.9, filed on October 14, 2002, herein incorporated herein by reference.

Please rewrite the paragraph on page 9, lines 21-23 as follows:

~~As a~~An example of a realization of the principle described on the basis of a CMOS camera, ~~reference shall be made to [1] in "A CMOS Image Sensor for High-Speed Imaging", IEEE International Solid-State Circuits Conference 2000:104-105, N. Stevanovic, M. Hillebrand, B.J. Hosticka, A. Teuner (2000).~~

Please delete the paragraph on page 10, lines 3-6.

Please delete the paragraph on page 12, lines 17-18.

Please rewrite the paragraph on page 20, lines 13-33 as follows:

As shown in figure 7, the modulated value of the electric current ΔI_{meas} is provided as sensor signal at an input 702 of the evaluation unit 700. The evaluation unit 700 has an operational amplifier 703. The operational amplifier 703 has an ~~an~~noninverting input 703a, at which the sensor signal ΔI_{meas} is provided. Furthermore, the operational amplifier 703 has a noninverting input 703b, to which a constant electrical reference potential V_{kai} is applied. The characteristic electrical voltage ΔV_{out} is provided at an output 703c of the operational amplifier 703. The output 703c of the operational amplifier 703 is fed back to the inverting input 703a of the operational amplifier 703 via the impedance Z 701. As is furthermore shown in figure 7, the electrical potential V_{kai} at the noninverting input 703b of the operational amplifier 703 is provided by means of the constant-voltage source 704. The constant-voltage source 704 is connected

between the electrical ground potential 605 and the noninverting input 703b of the operational amplifier 703.

Please rewrite the paragraph on page 24, line 22 – page 25, line 18 as follows:

For this purpose, the changeover element 807 is switched to the switch position "a" ~~(not shown in figure 8)~~. As a result, the constant voltage V_{drain} is impressed into all the circuit devices 801 of an associated row of circuit devices 801 using the detection constant-voltage source 811. The sensor arrangement 800 is sequentially read column by column. A column to be read is selected by the associated selection terminal 813 being brought to an electrical potential with a logic value "1", so that all the selection transistors 806 of the associated column of sensor arrangements 801 are brought to an electrically conductive state. If no sensor event takes place at a sensor element of a sensor device 801 of a selected column of sensor devices 801, then that DC component that was stored on the gate terminal 804c of the detection transistor 804 in the calibration phase flows through the activated sensor device 801. Parameter fluctuations, in particular of the detection transistors 804, are therefore compensated for. In other words, the output signal for an identical sensor event is identical and does not depend on the fluctuating parameters of the transistors. If a sensor event gives rise to a modulation of the electrical potential on a sensor element, then this results in a modulation of the electrical voltage at the gate terminal 804c of the associated detection transistor 804 and consequently of the electric current at the first source/drain terminal 804a of the detection transistor 804. This modulation is detected by means of the current detection unit 812 and can be amplified by external amplifier elements. The electric sensor current signal may optionally be converted into an electrical voltage (cf. evaluation unit 700 from figure 7).

Please delete the paragraphs on page 31, lines 1-6.